

D 8 substrate is one of a sapphire substrate, spinel substrate, perovskite yttrium aluminate substrate [or] and SiC substrate.

D 9 12. (Amended) The semiconductor device according to claim 9 wherein said semiconductor device is an FET using nitride III-V compound semiconductors.

Please add the following new Claim 24.

D 10 24. (New) A semiconductor device comprising:
a single-crystal substrate made of a material different from nitride III-V compound
semiconductors, and
a device formed on one major surface of said single-crystal substrate by using III-V compound
semiconductors,
wherein electrical connection to said device is made directly through a via hole formed in said
single-crystal substrate;.